

POST PLASMA CLEAN PROCESS FOR A HARDMASK

ABSTRACT OF THE DISCLOSURE

The present invention provides a process of manufacturing a semiconductor device that comprises a process of manufacturing a semiconductor device that includes plasma etching 250 through a patterned hardmask layer 210 located over a semiconductor substrate 225 wherein the plasma etching forms a modified layer 210a on the hardmask layer 210, and removing at least a substantial portion of the modified layer 210a by exposing the modified layer 210a to a post plasma clean process.